DATA SHEET

BSP106
N-channel enhancement mode vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

April 1995

Philips
Semiconductors

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N-channel enhancement mode vertical D-MOS transistor

BSP106

FEATURES

- Very low $R_{DS(on)}$
- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

DESCRIPTION

N-channel enhancement mode vertical D-MOS transistor in a miniature SOT223 envelope and intended for use in relay, high-speed and line transformer drivers.

PINNING - SOT223

PIN	DESCRIPTION
1	gate
2	drain
3	source
4	drain

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_{DS}	drain-source voltage	–	60	V
I_D	drain current	DC value	425	mA
$R_{DS(on)}$	drain-source on-resistance	I_D = 200 mA V_{GS} = 10 V	4	Ω
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA V_{GS} = V_{DS}	3	V

PIN CONFIGURATION

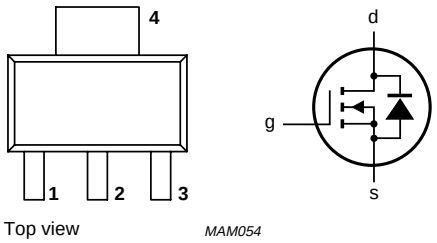


Fig.1 Simplified outline and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	60	V
V_{DG}	drain-gate voltage		–	60	V
$\pm V_{GSO}$	gate-source voltage		–	20	V
I_D	drain current	DC value	–	425	mA
I_{DM}	drain current	peak value	–	850	mA
P_{tot}	total power dissipation	up to T_{amb} = 25 °C (note 1)	–	1.5	W
T_{stg}	storage temperature range		–55	150	°C
T_j	junction temperature		–	150	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}a}$	from junction to ambient (note 1)	83.3	K/W

Note

1. Device mounted on an epoxy printed-circuit board 40 x 40 x 1.5 mm; mounting pad for the drain lead minimum 6 cm^2.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 10 μA V_{GS} = 0	60	90	–	V
I_{DSS}	drain-source leakage current	V_{DS} = 48 V V_{GS} = 0	–	–	1	μA
		V_{DS} = 25 V V_{GS} = 0	–	–	0.5	μA
$\pm I_{GSS}$	gate-source leakage current	V_{DS} = 0 $\pm V_{GS}$ = 15 V	–	–	10	nA
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA $V_{GS} = V_{DS}$	0.8	–	3	V
$R_{DS(on)}$	drain-source on-resistance	I_D = 200 mA V_{GS} = 10 V	–	2.5	4	Ω
$\lvert Y_{fs} \rvert$	transfer admittance	I_D = 200 mA V_{DS} = 10 V	100	200	–	mS
C_{iss}	input capacitance	V_{DS} = 10 V V_{GS} = 0 f = 1 MHz	–	25	40	pF
C_{oss}	output capacitance	V_{DS} = 10 V V_{GS} = 0 f = 1 MHz	–	22	30	pF
C_{rss}	feedback capacitance	V_{DS} = 10 V V_{GS} = 0 f = 1 MHz	–	6	10	pF
Switching times (see Figs 2 **and** 3**)**						
t_{on}	turn-on time	I_D = 200 mA V_{DD} = 50 V V_{GS} = 0 to 10 V	–	2	5	ns
t_{off}	turn-off time	I_D = 200 mA V_{DD} = 50 V V_{GS} = 0 to 10	–	10	15	ns

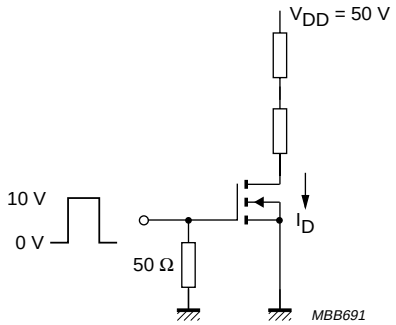


Fig.2 Switching time test circuit.

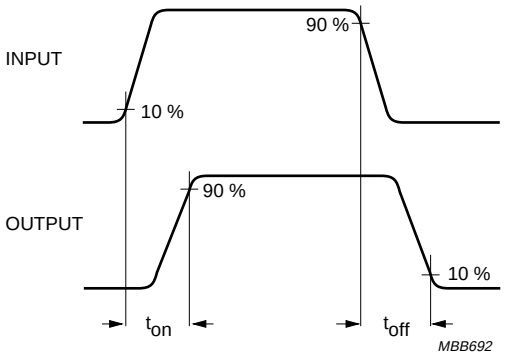


Fig.3 Input and output waveforms.

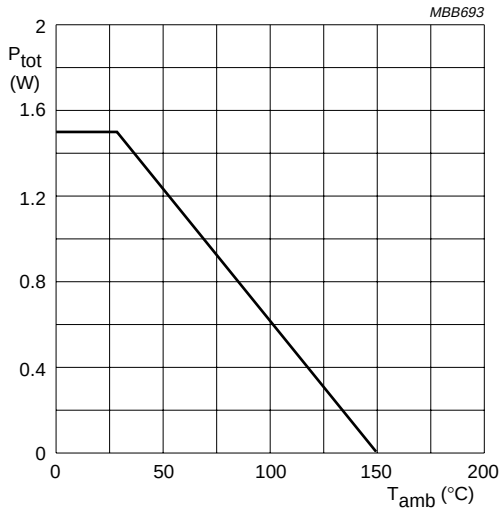


Fig.4 Power derating curve.

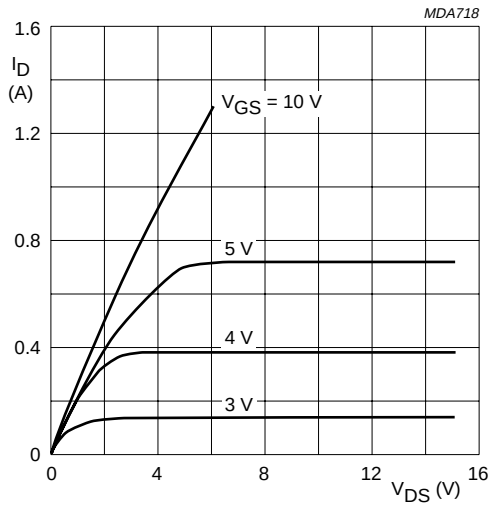


Fig.5 Typical output characteristics; T_j = 25 °C.

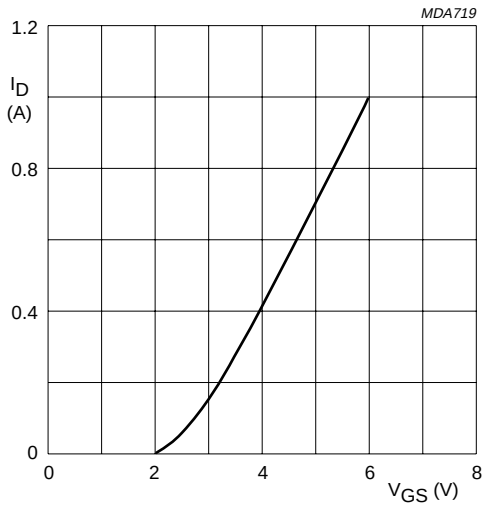


Fig.6 Typical transfer characteristic; V_{DS} = 10 V; T_j = 25 °C.

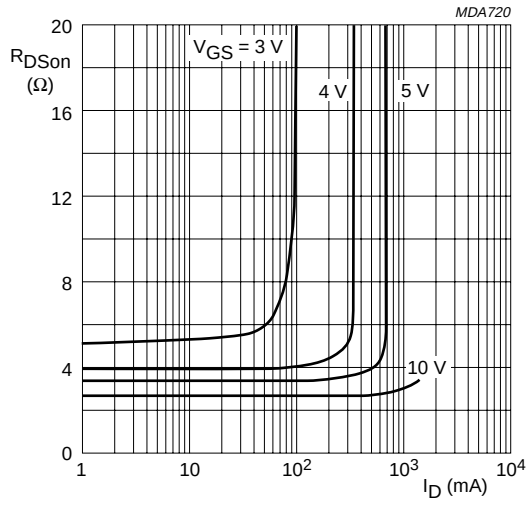


Fig.7 Typical on-resistance as a function of drain current; T_j = 25 °C.

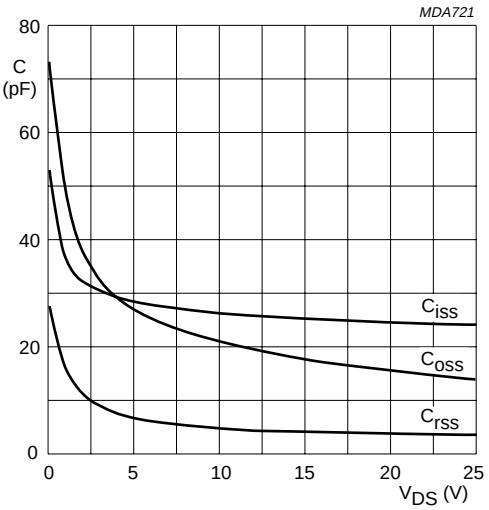


Fig.8 Typical capacitances as a function of drain-source voltage; V_{GS} = 0; f = 1 MHz; T_j = 25 °C.

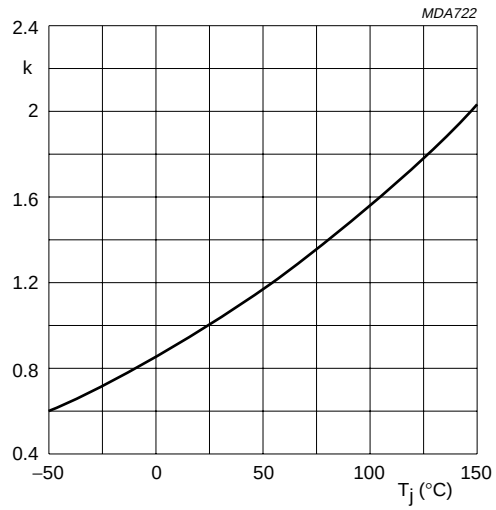


Fig.9 Temperature coefficient of drain-source on-resistance;

$$k = \frac{R_{DS(on)} \text{ at } T_j}{R_{DS(on)} \text{ at } 25\ °C};$$

typical $R_{DS(on)}$ at 200 mA/10 V.

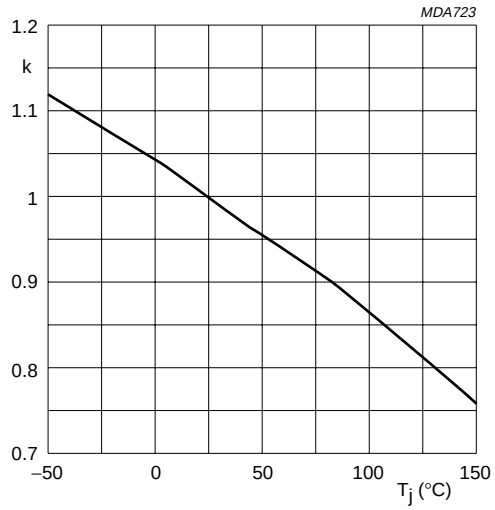


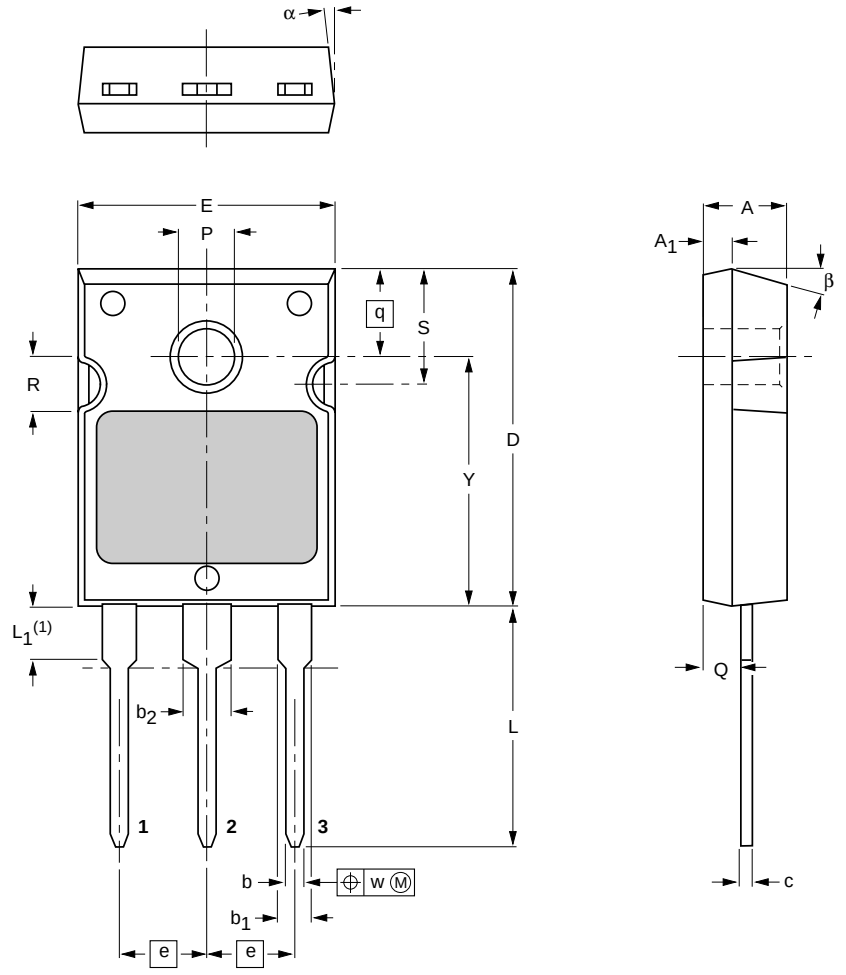
Fig.10 Temperature coefficient of gate-source threshold voltage;

$$k = \frac{V_{GS(th)} \text{ at } T_j}{V_{GS(th)} \text{ at } 25\ ^\circ C};$$

$V_{GS(th)}$ at 1 mA.

PACKAGE OUTLINES

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-247 **SOT429**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	b_2	c	D	E	e	L	L_1(1)	P	Q	q	R	S	w	Y	α	β
mm	5.3 4.7	1.9 1.7	1.2 0.9	2.2 1.8	3.2 2.8	0.9 0.6	21 20	16 15	5.45	16 15	4.0 3.6	3.7 3.3	2.6 2.4	5.3	3.5 3.3	7.5 7.1	0.4	15.7 15.3	6° 4°	17° 13°

Note

1. Tinning of terminals are uncontrolled within zone L_1.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT429		TO-247				98-03-24

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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